

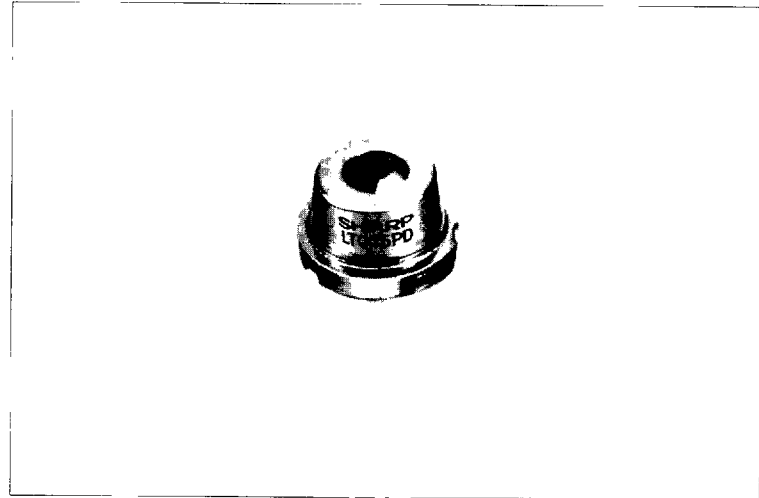
LT015PD

Features

- High output (maximum optical power output 40 mW)
- Wavelength: 830nm
- Single transverse mode

Applications

- Optical disk memories
- Medical apparatus
- Optical floppy disks
- Optical memory cards
- Information processing equipment



Absolute Maximum Ratings

(T_c = 25°C)

Parameter	Symbol	Ratings	Units
Optical power output	P _o	40	mW
Reverse voltage	Laser	2	V
	PIN	30	
Operating temperature*1	T _{opr}	-10 to +50	°C
Storage temperature*1	T _{stg}	-40 to +85	°C

*1 Case temperature

Electro-optical Characteristics*1

(T_c = 25°C)

Parameter	Symbol	Condition	Ratings			Units		
			MIN	TYP	MAX			
Threshold current	I _{th}	—	—	60	80	mA		
Operating current	I _{op}	P _o = 30mW	—	95	130	mA		
Operating voltage	V _{op}	P _o = 30mW	—	1.75	2.2	V		
Wavelength*2	λ _p	P _o = 30mW	815	830	845	nm		
Monitor current	I _m	P _o = 30mW V _R = 15V	30	100	380	μA		
Radiation characteristics	Angle*3	Parallel to junction	θ _{//}	P _o = 30mW	8	9.5	14	deg
		Perpendicular to junction	θ _⊥	P _o = 30mW	20	27	38	deg
	Ripple	P _o = 30mW	—	—	±20	%		
Emission point accuracy	Angle	Δφ _{//}	P _o = 30mW	—	—	±2	deg	
		Δφ _⊥	P _o = 30mW	—	—	±3	deg	
	Position	Δx, Δy, Δz	—	—	—	±80	μm	
Differential efficiency	η	20mW I _F (30mW) - I _F (10mW)	0.5	0.8	1.1	mW/mA		

*1 Initial value

*3 Angle at 50% peak intensity (full width at half-maximum)

*2 Single transverse mode

Electrical Characteristics of Photodiode

(T_c = 25°C)

Parameter	Symbol	Condition	Ratings			Units
			MIN	TYP	MAX	
Sensitivity	S	V _R = 15V	—	3.3	—	μA/mW
Dark current	I _D	V _R = 15V	—	—	150	nA
Terminal capacitance	C _t	V _R = 15V	—	18	20	pF

Common Data

Fig. 94-1 Optical Power Output Dependence of Far-Field Pattern

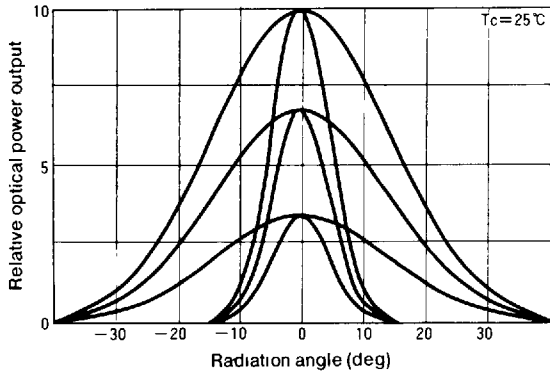


Fig. 94-4 Coupling Efficiency

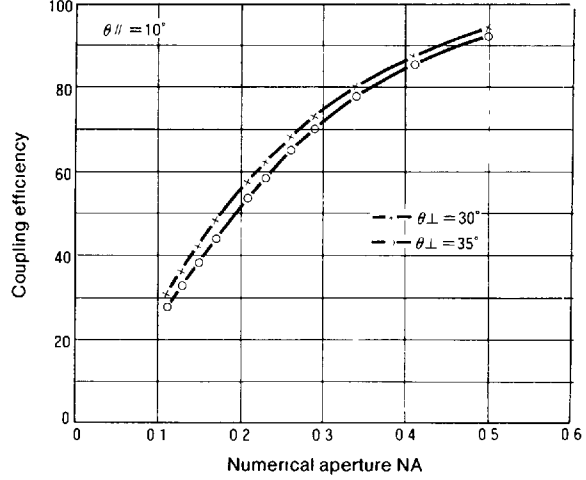


Fig. 94-2 Polarization Ratio vs. Optical Power Output (LT026 series, LT023 series)

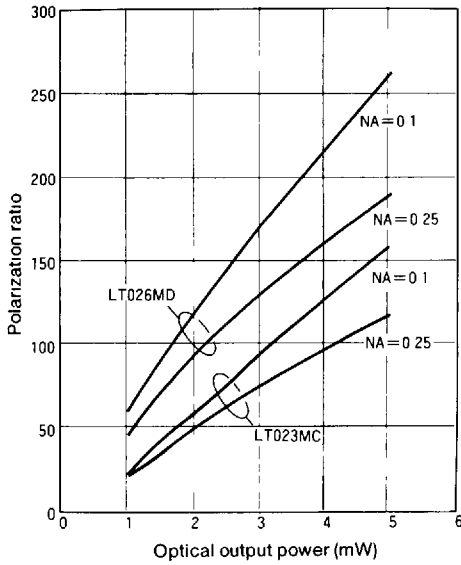


Fig. 94-5 Frequency Response

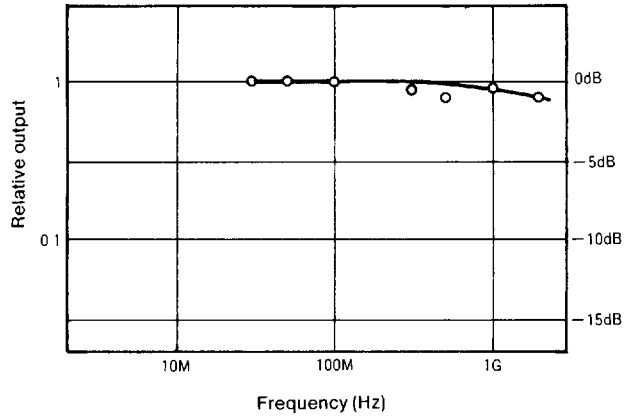
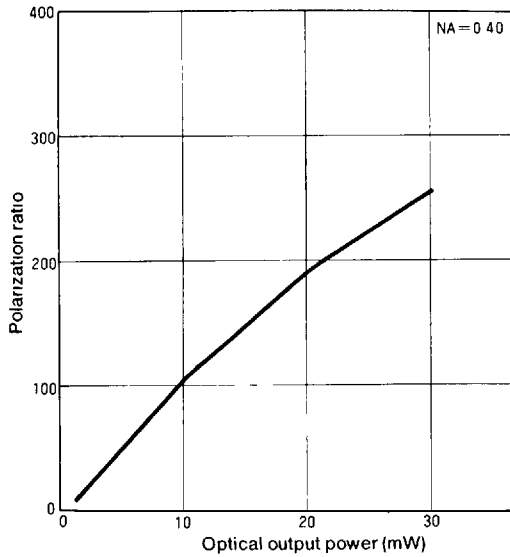


Fig. 94-3 Polarization Ratio vs. Optical Power Output (LT024 series, LT015 series)



Note All data on this page is typical only, and is not intended as a specification. The shapes of these curves can be used as a general reference, but the actual characteristics will vary from device to device.

Built-in PIN Photodiode Characteristics

Fig. 95-1 Photodiode Frequency Response Characteristic

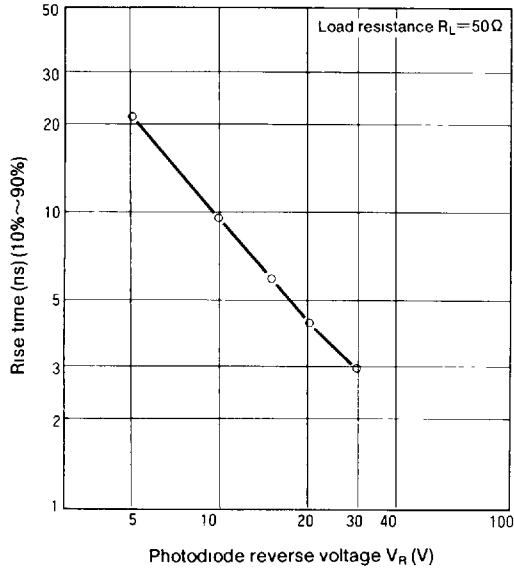
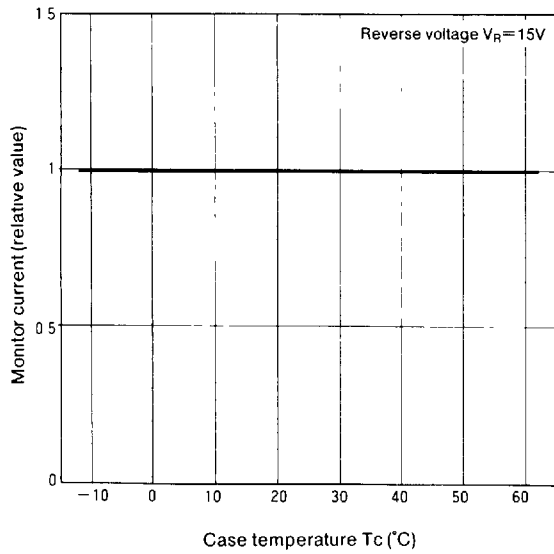


Fig. 95-2 Photodiode Temperature Characteristic



Note: All data on this page is typical only, and is not intended as a specification. The shapes of these curves can be used as a general reference, but the actual characteristics will vary from device to device.

Outline Dimensions

Unit: mm

Fig. 98-1 Standard Type (C Type)

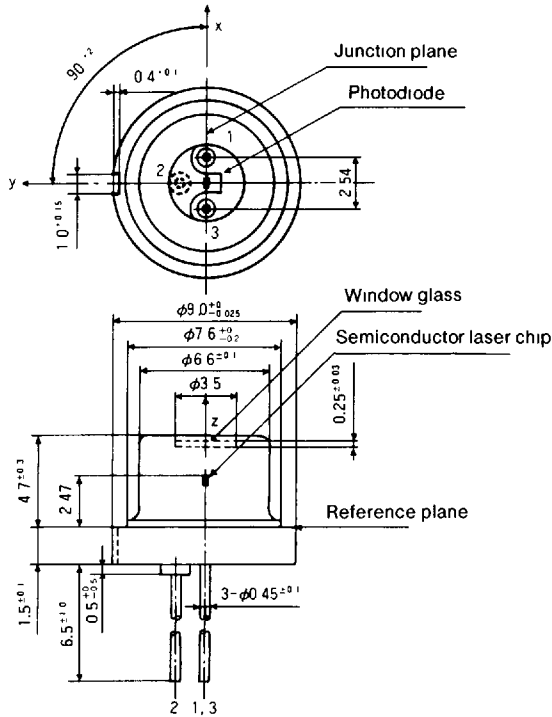


Fig. 98-2 Low-Cap Type (D Type)

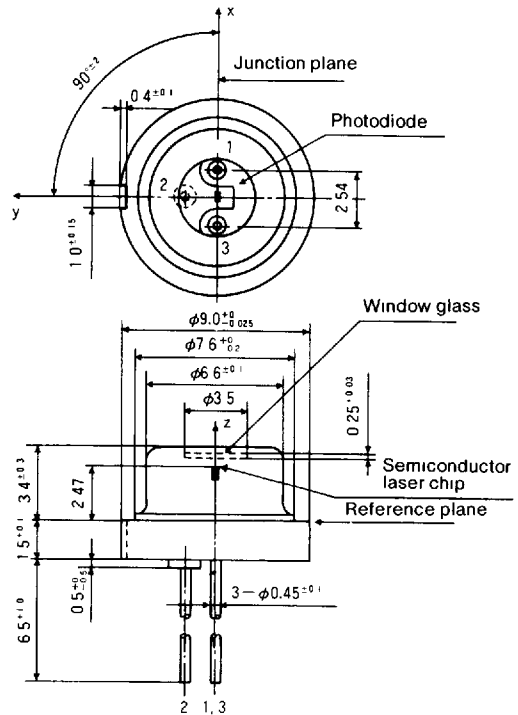


Fig. 98-3 Fin-Equipped Type (F Type)

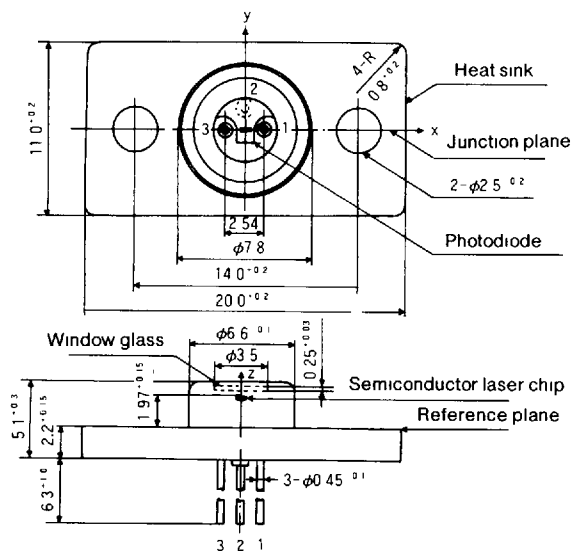
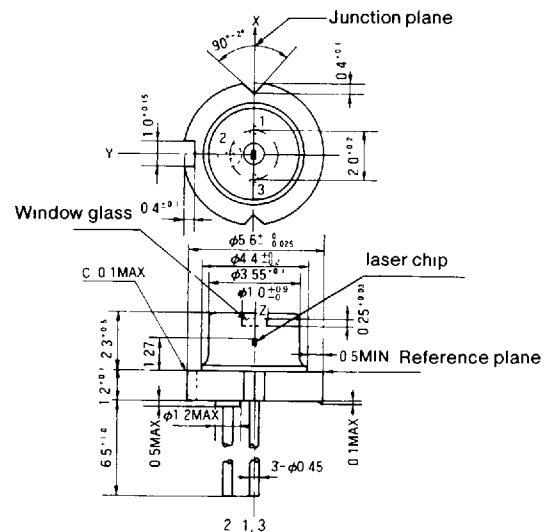


Fig. 98-4 Compact Package Type (S Type)



Terminal connections

